30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_A = +25°C
30V	21mΩ @ V_{GS} = 10V	8.5A
	35mΩ @ V_{GS} = 4.5V	6.6A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

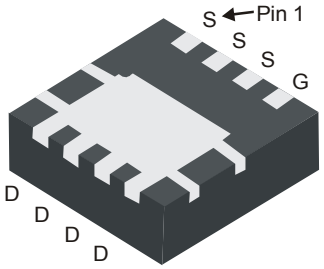
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

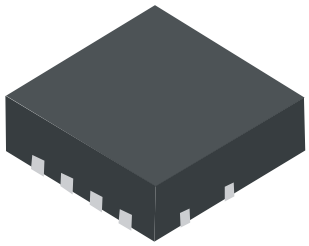
- Low $R_{DS(ON)}$ – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

Mechanical Data

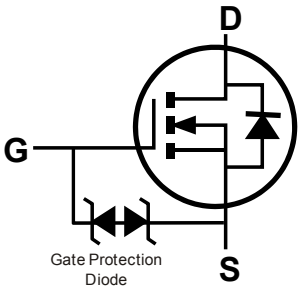
- Case: POWERDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (approximate)



Bottom View



Top View



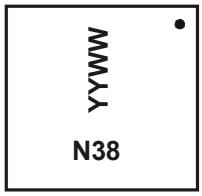
Top View
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3018SFG-7	POWERDI®3333-8	2000/Tape & Reel
DMN3018SFG-13	POWERDI®3333-8	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N38 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last digit of year (ex: 11 = 2011)
WW = Week code (01 ~ 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±25	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	8.5 6.8	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	11.3 9.1	A
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	6.6 5.3	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	8.7 7.0	A
Maximum Continuous Body Diode Forward Current (Note 4)			I_S	2.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	60	A
Avalanche Current (Note 7) L = 0.1mH			I_{AS}	18	A
Avalanche Energy (Note 7) L = 0.1mH			E_{AS}	16	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_D	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	126	°C/W
	t<10s		71	
Total Power Dissipation (Note 6)		P_D	2.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	56	°C/W
	t<10s		31	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	7.0	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 24V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1	1.7	2.1	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	16	21	mΩ	V_{GS} = 10V, I_D = 10A
		—	21	35		V_{GS} = 4.5V, I_D = 8.5A
Diode Forward Voltage	V_{SD}	0.5	—	1.2	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	697	—	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	97	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	67	—	pF	
Gate resistance	R_g	—	1.47	—	Ω	V_{DS} = 0V, V_{GS} = 0V,f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	6.0	—	nC	V_{GS} = 10V, V_{DS} = 15V, I_D = 9A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	13.2	—	nC	
Gate-Source Charge	Q_{gs}	—	2.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.8	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	4.3	—	ns	V_{DD} = 15V, V_{GS} = 10V, R_L = 15Ω,I_D = 1A, R_G = 6Ω
Turn-On Rise Time	t_r	—	4.4	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	20.1	—	ns	
Turn-Off Fall Time	t_f	—	4.1	—	ns	
Reverse Recovery Time	T_{rr}	—	7.3	—	ns	I_F = 9A, di/dt = 500A/µs
Reverse Recovery Charge	Q_{rr}	—	7.9	—	nC	

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

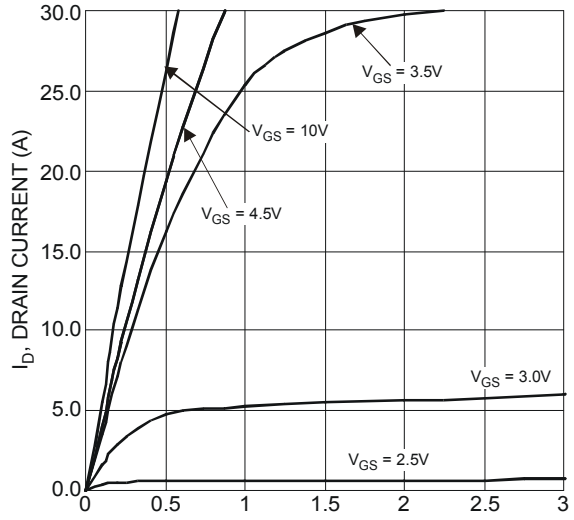


Figure 1 Typical Output Characteristics

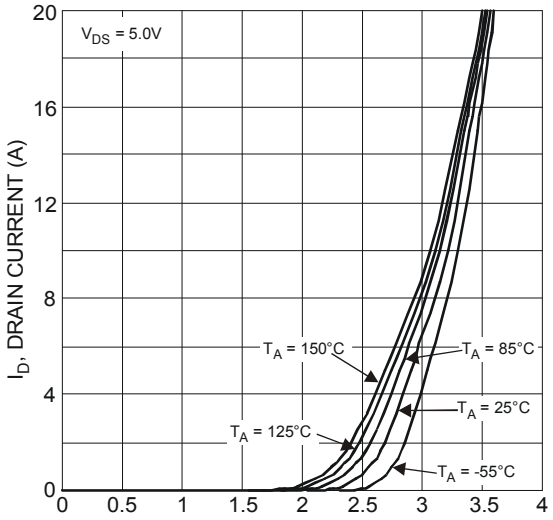


Figure 2 Typical Transfer Characteristics

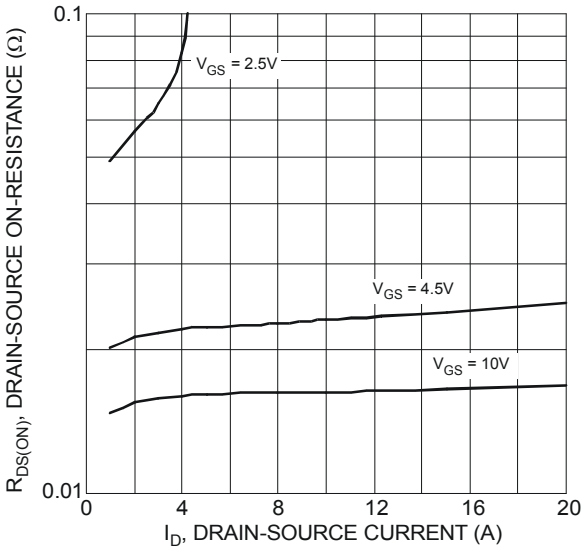


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

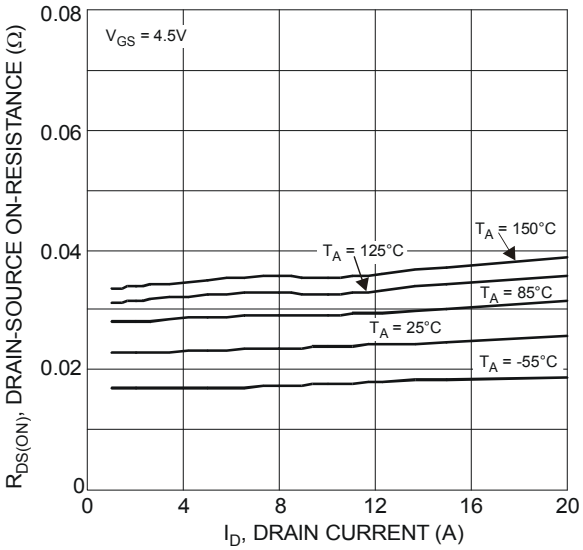


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

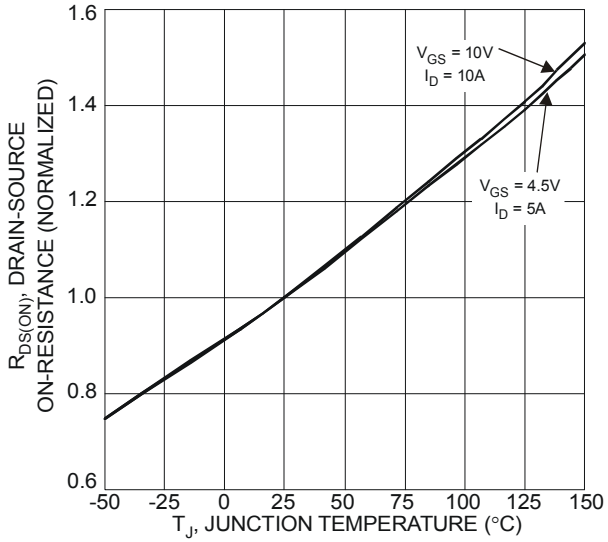


Figure 5 On-Resistance Variation with Temperature

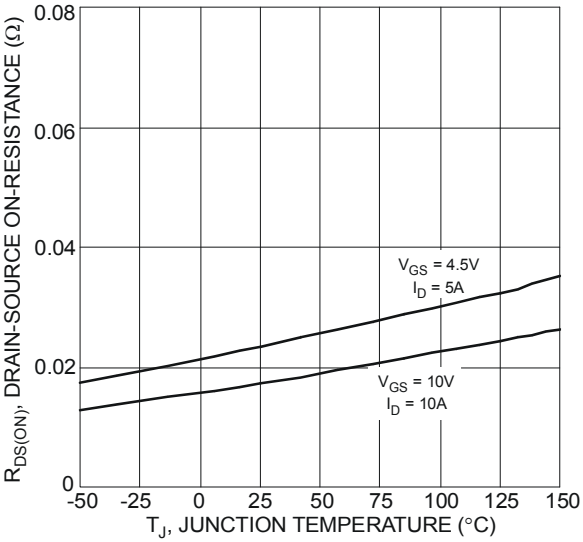


Figure 6 On-Resistance Variation with Temperature

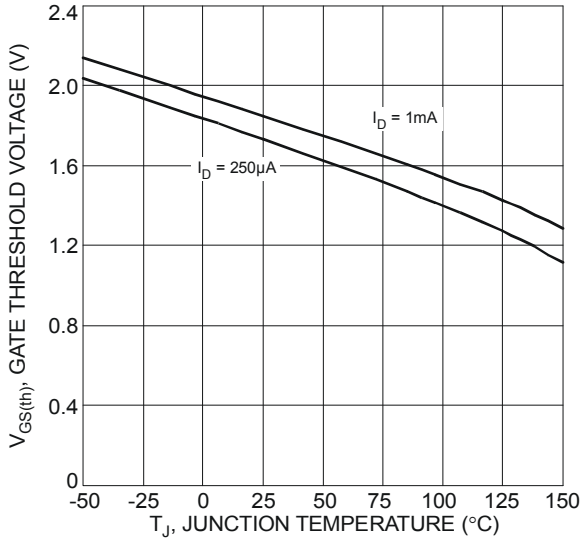


Figure 7 Gate Threshold Variation vs. Ambient Temperature

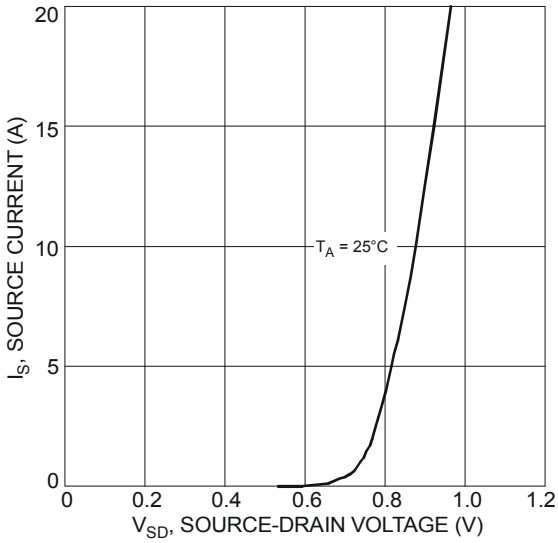


Figure 8 Diode Forward Voltage vs. Current

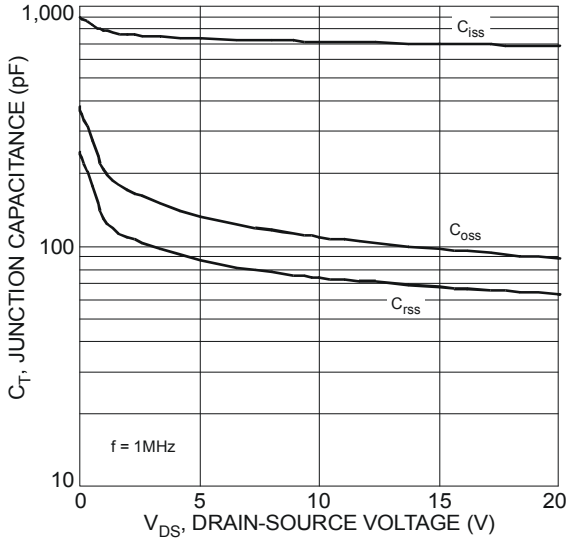


Figure 9 Typical Junction Capacitance

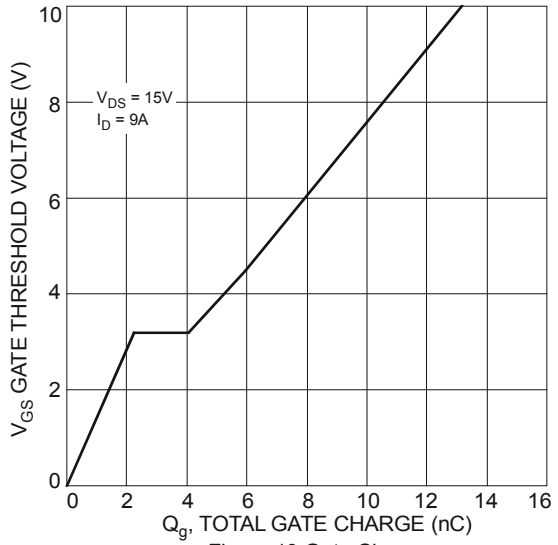


Figure 10 Gate Charge

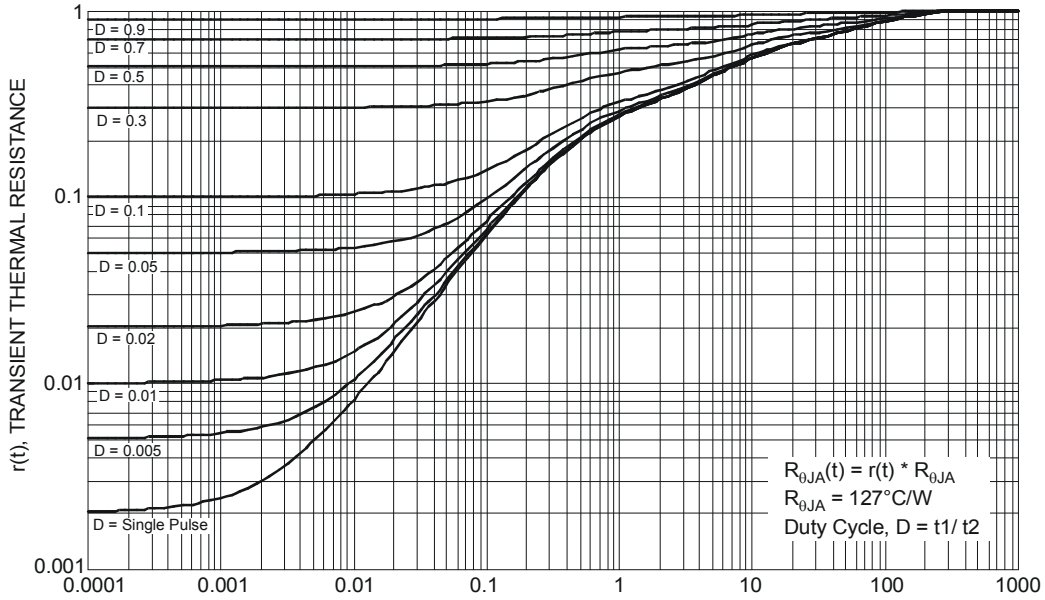
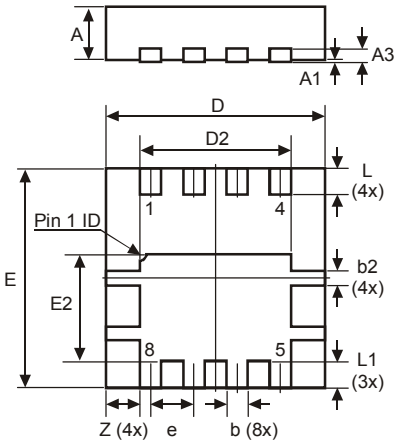


Figure 11 Transient Thermal Resistance

Package Outline Dimensions

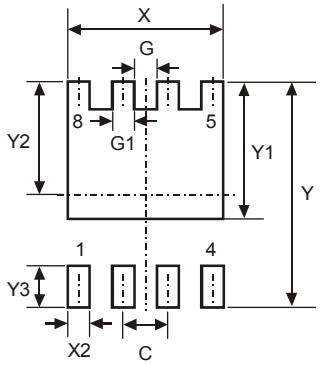
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI®3333-8			
Dim	Min	Max	Typ
D	3.25	3.35	3.30
E	3.25	3.35	3.30
D2	2.22	2.32	2.27
E2	1.56	1.66	1.61
A	0.75	0.85	0.80
A1	0	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	–	–	0.20
L	0.35	0.45	0.40
L1	–	–	0.39
e	–	–	0.65
Z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
X	2.370
X2	0.420

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